

BAV99WT1G, SBAV99WT1G, BAV99RWT1G, SBAV99RWT1G

Dual Series Switching Diodes

The BAV99WT1 is a smaller package, equivalent to the BAV99LT1.

Features

- These Devices are Pb-Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

Suggested Applications

- ESD Protection
- Polarity Reversal Protection
- Data Line Protection
- Inductive Load Protection
- Steering Logic

MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-Repetitive Peak Forward Current $t = 1.0 \mu s$ $t = 1.0 ms$ $t = 1.0 s$	I_{FSM}	2.0 1.0 0.5	A

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

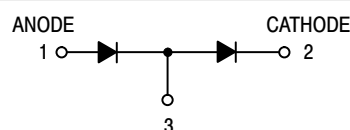


ON Semiconductor®

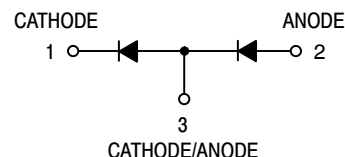
<http://onsemi.com>



SC-70
CASE 419

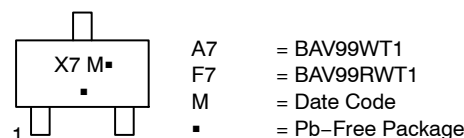


BAV99WT1
SC-70, CASE 419, STYLE 9



BAV99RWT1
SC-70, CASE 419, STYLE 10

MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping†
BAV99WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SBAV99WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
BAV99RWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SBAV99RWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BAV99WT1G, SBAV99WT1G, BAV99RWT1G, SBAV99RWT1G

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	200 1.6	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

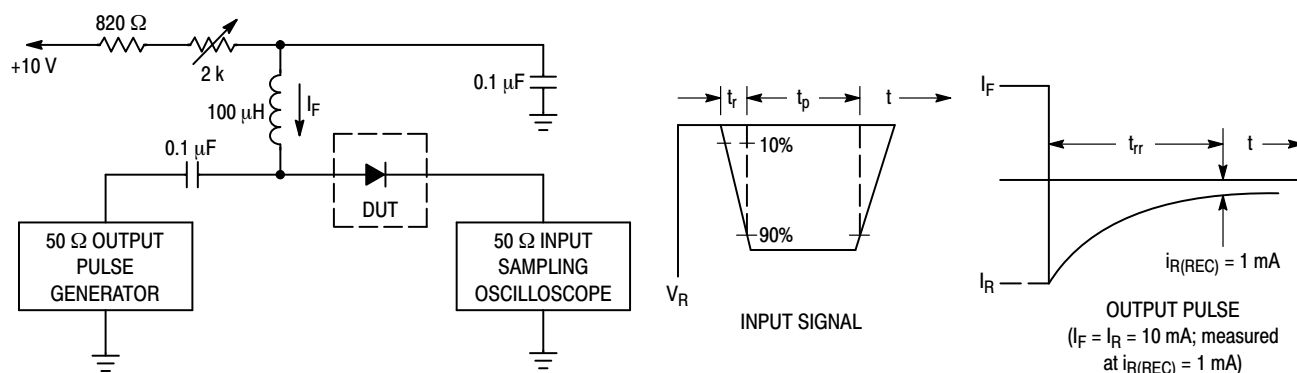
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Reverse Breakdown Voltage ($I_{(BR)} = 100 \mu\text{A}$)	$V_{(BR)}$	70	–	Vdc
Reverse Voltage Leakage Current ($V_R = 70 \text{ Vdc}$) ($V_R = 25 \text{ Vdc}$, $T_J = 150^\circ\text{C}$) ($V_R = 70 \text{ Vdc}$, $T_J = 150^\circ\text{C}$)	I_R	– – –	2.5 30 50	μAdc
Diode Capacitance ($V_R = 0$, $f = 1.0 \text{ MHz}$)	C_D	–	1.5	pF
Forward Voltage ($I_F = 1.0 \text{ mAdc}$) ($I_F = 10 \text{ mAdc}$) ($I_F = 50 \text{ mAdc}$) ($I_F = 150 \text{ mAdc}$)	V_F	– – – –	715 855 1000 1250	mVdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mAdc}$, $i_{R(REC)} = 1.0 \text{ mAdc}$) (Figure 1) $R_L = 100 \Omega$	t_{rr}	–	6.0	ns
Forward Recovery Voltage ($I_F = 10 \text{ mA}$, $t_r = 20 \text{ ns}$)	V_{FR}	–	1.75	V

- FR-5 = $1.0 \times 0.75 \times 0.062 \text{ in.}$
- Alumina = $0.4 \times 0.3 \times 0.024 \text{ in.}$ 99.5% alumina.



- Notes: (a) A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA.
 (b) Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
 (c) $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

BAV99WT1G, SBAV99WT1G, BAV99RWT1G, SBAV99RWT1G

CURVES APPLICABLE TO EACH DIODE

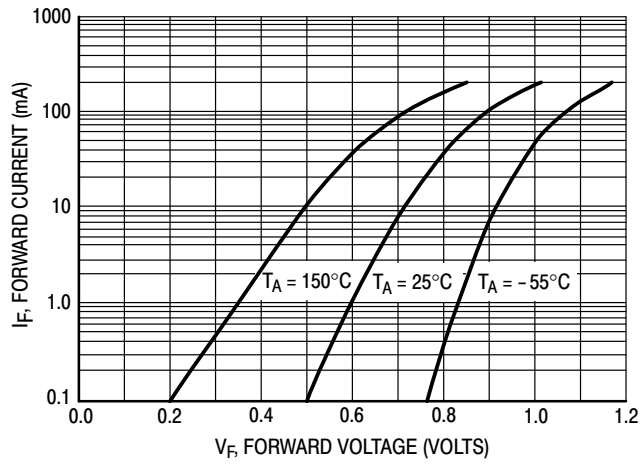


Figure 2. Forward Voltage

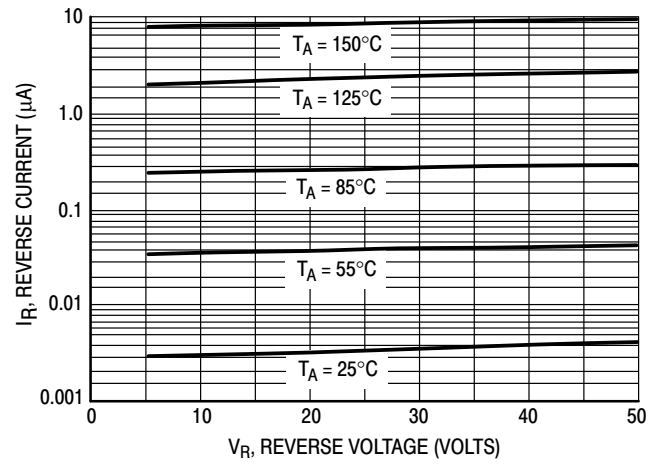


Figure 3. Leakage Current

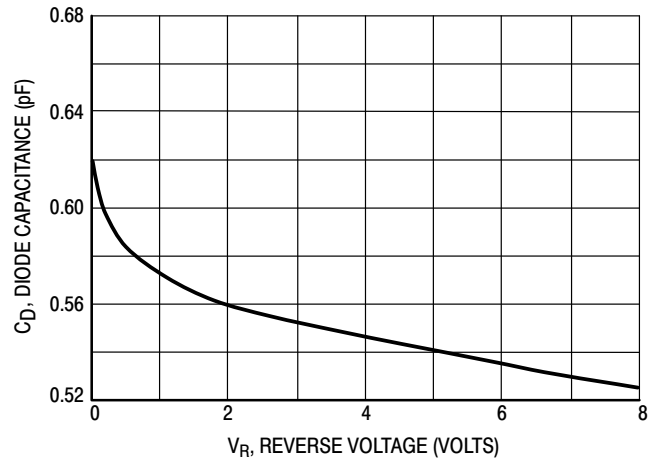
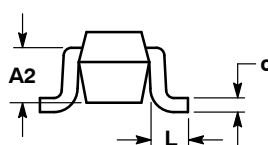
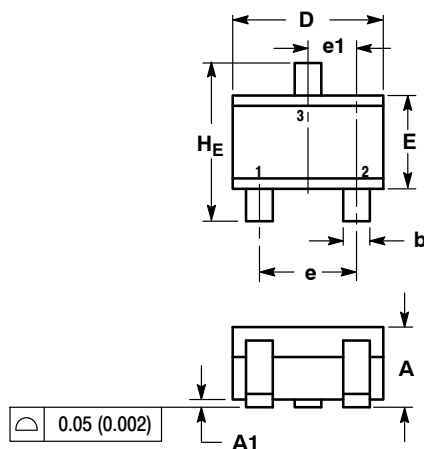


Figure 4. Capacitance

BAV99WT1G, SBAV99WT1G, BAV99RWT1G, SBAV99RWT1G

PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 ISSUE N



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

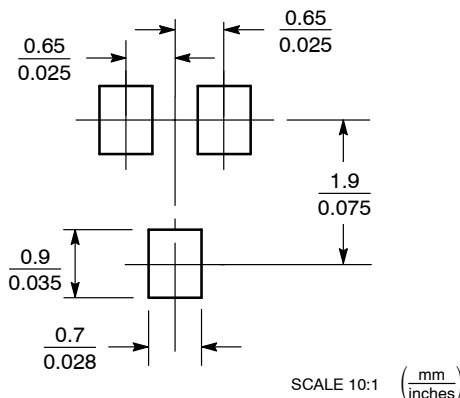
STYLE 9:

- PIN 1: ANODE
- CATHODE
- CATHODE-ANODE

STYLE 10:

- PIN 1: CATHODE
- ANODE
- ANODE-CATHODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marketing.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local
Sales Representative